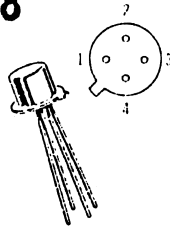


2N3307 (SILICON)

2N3308



STYLE 10  
 PIN 1. EMITTER  
 2. BASE  
 3. COLLECTOR  
 4. CASE

PNP silicon annular transistors for high-gain, low-noise amplifier, oscillator, mixer and frequency multiplier applications.

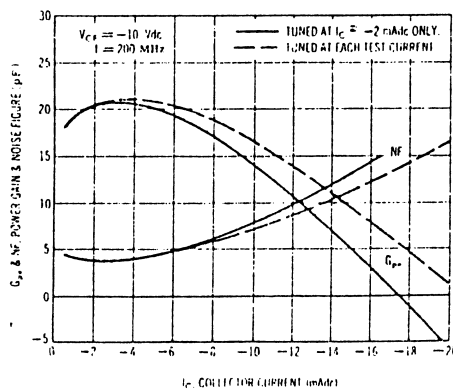
(TO-72)

\*MAXIMUM RATINGS

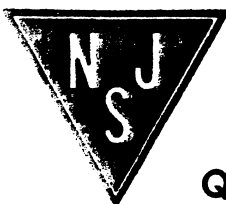
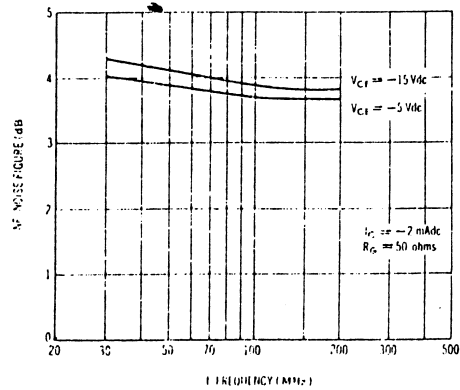
Rating	Symbol	Value		Unit
		2N3307	2N3308	
Collector-Base Voltage	$V_{CB}$	40	30	Vdc
Collector-Emitter Voltage	$V_{CES}$	40	30	Vdc
Collector-Emitter Voltage	$V_{CEO}$	35	25	Vdc
Emitter-Base Voltage	$V_{EB}$	3.0		Vdc
Collector Current	$I_C$	50		mAdc
Power Dissipation at $T_C = 25^\circ\text{C}$ Derate above $25^\circ\text{C}$	$P_D$	300		mW
		1.71		mW/ $^\circ\text{C}$
Power Dissipation at $T_A = 25^\circ\text{C}$ Derate above $25^\circ\text{C}$	$P_D$	200		mW
		1.14		mW/ $^\circ\text{C}$
Junction Temperature	$T_J$	200		$^\circ\text{C}$
Storage Temperature Range	$T_{stg}$	-65 to +200		$^\circ\text{C}$

\*Indicates JEDEC Registered Data

COMMON EMITTER AVERAGE SMALL POWER GAIN  
 & NOISE FIGURE versus COLLECTOR CURRENT



NOISE FIGURE versus FREQUENCY



ELECTRICAL CHARACTERISTICS (T<sub>A</sub> = 25°C unless otherwise noted)

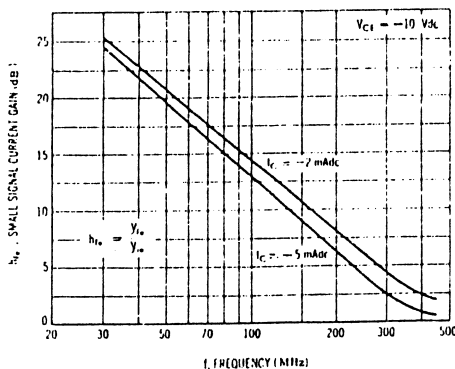
Characteristic	Symbol	Test Conditions	Min	Typ	Max	Unit
Collector-Base Breakdown Voltage	V <sub>CB0</sub>	I <sub>C</sub> = 10 μAde, I <sub>E</sub> = 0	2N3307 2N3308 40 30	-	-	Vdc
Collector-Emitter Breakdown Voltage	V <sub>CES</sub>	I <sub>C</sub> = 10 μAde, V <sub>BE</sub> = 0	2N3307 2N3308 40 30	-	-	Vdc
Collector-Emitter Breakdown Voltage	V <sub>CEO</sub>	I <sub>C</sub> = 2.0 mAde, I <sub>B</sub> = 0	2N3307 2N3308 35 25	-	-	Vdc
Emitter-Base Breakdown Voltage	V <sub>EBO</sub>	I <sub>E</sub> = 10 μAde, I <sub>C</sub> = 0	Both Types	-	-	Vdc
Collector Cutoff Current	I <sub>CHO</sub>	V <sub>CB</sub> = 15 Vdc V <sub>CB</sub> = 15 Vdc, T = 150 °C	Both Types 2N3307	- 0.001 0.5	0.010 3.0	μAde
DC Current Gain	h <sub>FE</sub>	V <sub>CE</sub> = 10 Vdc, I <sub>C</sub> = 2 mAde	2N3307 2N3308	10 25	250 250	-
Collector-Emitter Saturation Voltage	V <sub>CE(sat)</sub>	I <sub>C</sub> = 3 mAde, I <sub>B</sub> = 0.6 mAde	Both Types	-	0.4	Vdc
Base-Emitter Saturation Voltage	V <sub>BE(sat)</sub>	I <sub>C</sub> = 3 mAde, I <sub>B</sub> = 0.6 mAde	Both Types	-	1.0	Vdc
AC Current Gain	h <sub>fe</sub>	V <sub>CE</sub> = 10 Vdc, I <sub>C</sub> = 2 mAde, f = 1 kHz	2N3307 2N3308	40 25	250 250	-
Output Capacitance(1)	C <sub>ob</sub>	V <sub>CB</sub> = 10 Vdc, I <sub>E</sub> = 0, f = 0.1 MHz	2N3307 2N3308	- 1.2	1.3 1.6	pF
Collector-Base Time Constant	r <sub>b</sub> 'C <sub>c</sub>	V <sub>CB</sub> = 10 Vdc, I <sub>C</sub> = 2 mAde, f = 31.8 MHz	2N3307 2N3308	2.0 2.0	15 20	ps
Current Gain-Bandwidth Product	f <sub>T</sub>	V <sub>CE</sub> = 10 Vdc, I <sub>C</sub> = 2 mAde, f = 100 MHz	Both Types	300	1200	MHz
Maximum Frequency of Oscillation	f <sub>max</sub>	V <sub>CE</sub> = 10 Vdc, I <sub>C</sub> = 2 mAde	Both Types	-	2000	MHz
Power Gain	G <sub>p</sub>	V <sub>CE</sub> = 10 Vdc, I <sub>C</sub> = 2 mAde, f = 200 MHz	Both Types	17	24	dB
Noise Figure	NF	V <sub>CE</sub> = 10 Vdc, I <sub>C</sub> = 2 mAde, f = 200 MHz	2N3307 2N3308	- 5.0	4.5 6.0	dB
Power Gain (AGC) (2)	G <sub>p</sub>	V <sub>CE</sub> = 5.0 Vdc, I <sub>C</sub> = 20 mAde, f = 200 MHz	2N3307 2N3308	- 0	0 -	dB

(1) C<sub>ob</sub> is measured in guarded circuit such that the can capacitance is not included.

(2) AGC is obtained by increasing I<sub>C</sub>. The circuit remains adjusted for V<sub>CE</sub> = -10 Vdc, I<sub>C</sub> = -2 mAde operation.

\* Indicates JEDEC Registered Data

SMALL SIGNAL CURRENT GAIN versus FREQUENCY



MAXIMUM AVAILABLE GAIN versus FREQUENCY

